# BTA312-600B

## **3Q Hi-Com Triac**

Rev. 02 — 29 November 2010

Product data sheet

### 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber.

#### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

### 1.3 Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g.
   DC motors and solenoids

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 4; see Figure 5	-	-	95	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 101 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	12	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N. 1
2	T2	main terminal 2	mb	T2—T1
2	T2	main terminal 2		`G sym051
3	G	gate		
mb	T2	mounting base; main terminal 2		
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA312-600B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage	)	-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 101 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	12	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25  \text{C}$ ; $t_p = 20 \text{ ms}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	95	Α
		full sine wave; $T_{j(init)} = 25 \text{ C}$ ; $t_p = 16.7 \text{ ms}$	-	105	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	45	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	$\mathcal C$
Tj	junction temperature		-	125	$\mathcal C$

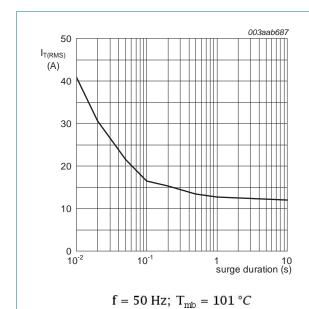


Fig 1. RMS on-state current as a function of surge duration; maximum values

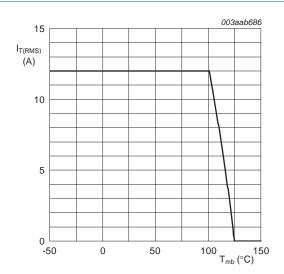
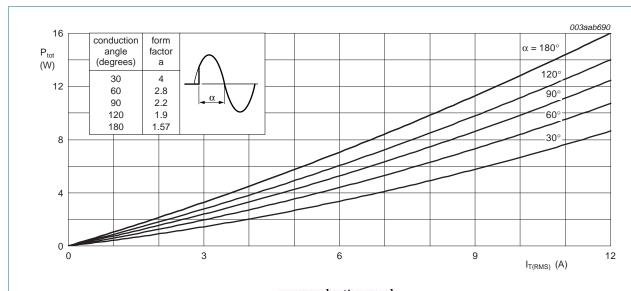
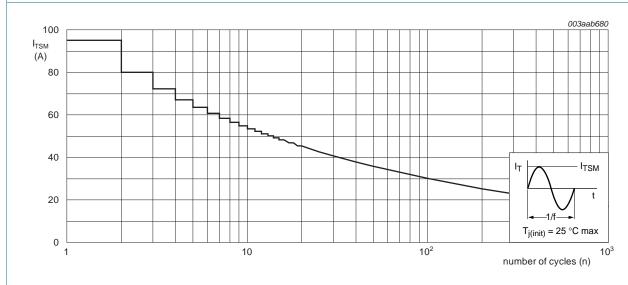


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values



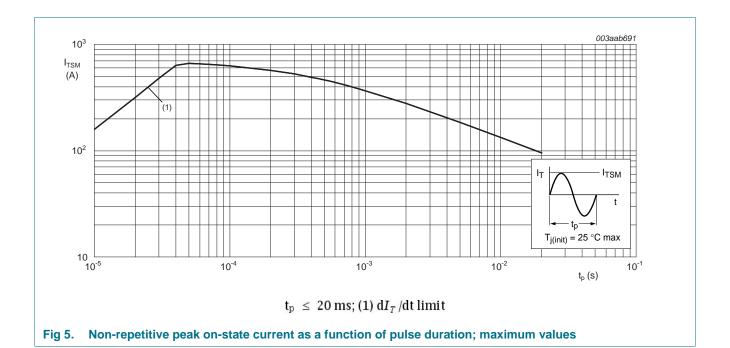
 $\alpha$  = conduction angle

Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	full cycle; see Figure 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; see Figure 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

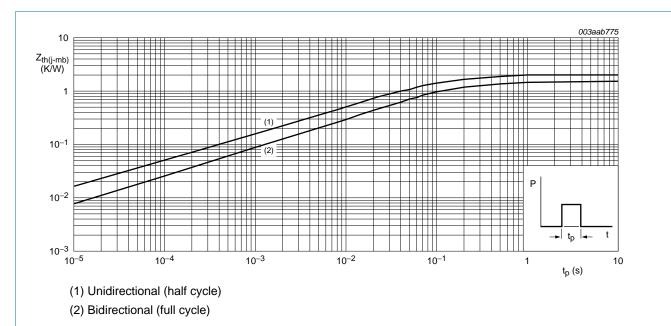
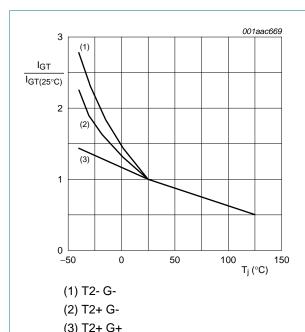


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 7}}{}$	2	-	50	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 8}}{\text{ C}}$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	60	mA
l <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C};$ see Figure 9	-	-	60	mA
V <sub>T</sub>	on-state voltage	$I_T = 15 \text{ A}; T_j = 25 \text{ C}; \text{ see } \frac{\text{Figure } 10}{}$	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ C};$ see Figure 11	-	8.0	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ C};$ see Figure 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 ℃	-	0.1	0.5	mΑ
Dynamic ch	naracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; exponential waveform; gate open circuit	1000	2000	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ C}; I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s};$ gate open circuit; "without snubber" condition	30	-	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



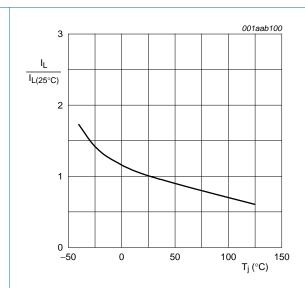
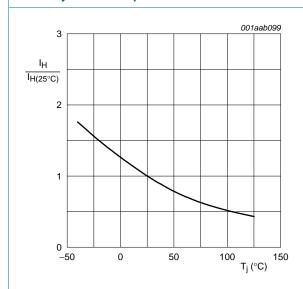


Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature



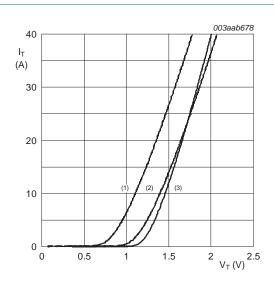


Fig 9. Normalized holding current as a function of junction temperature

Vo = 1.127 V; Rs = 0.027  $\Omega$ (1) Tj = 125 °C; typical values (2) Tj = 125 °C; maximum values (3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

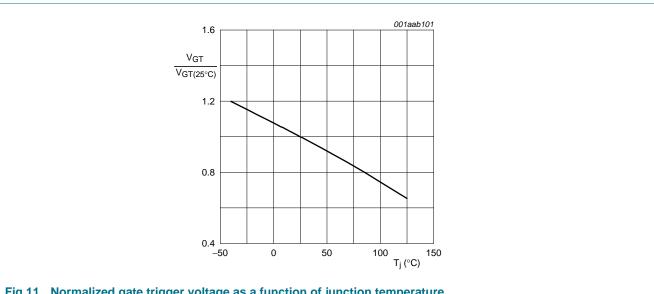
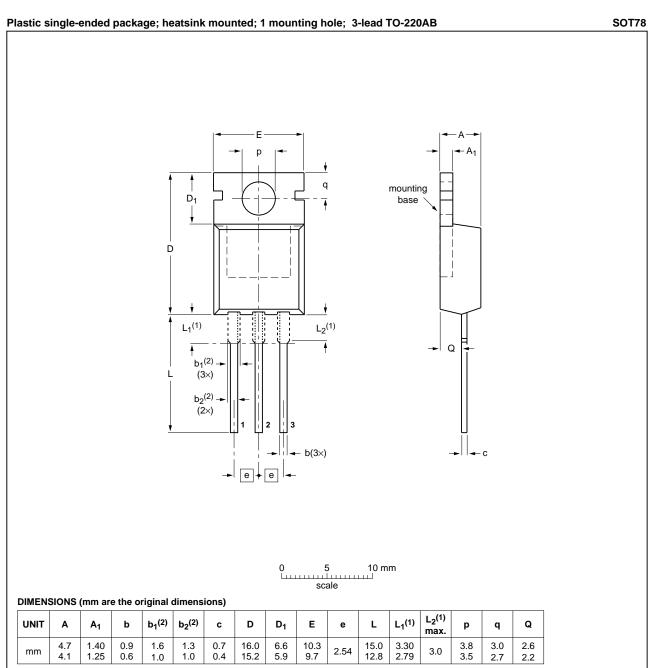


Fig 11. Normalized gate trigger voltage as a function of junction temperature

## 7. Package outline



#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DAT		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13	

Fig 12. Package outline SOT78 (TO-220AB)

BTA312-600B

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BTA312-600B v.2	20101129	Product data sheet	-	BTA312_SER_B_C v.1		
Modifications: • Type number BTA312-600B separated from data sheet BTA312_SER_B_C v.1.						
<ul> <li>Various changes to content.</li> </ul>						
BTA312_SER_B_C v.1	20070313	Product data sheet	-	-		

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#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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